

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. - 13. (canceled).

14. (new): A p-type Group III nitride semiconductor composed of AlGaN, which has a resistivity of 50  $\Omega\text{cm}$  to 2,000  $\Omega\text{cm}$  and contains a p-type dopant at a concentration of  $1 \times 10^{18} \text{ cm}^{-3}$  to  $1 \times 10^{21} \text{ cm}^{-3}$  and hydrogen atom in an amount which is more than 1/5 the p-type dopant concentration and which is less than the p-type dopant concentration.

15. (new): A method for producing a Group III nitride semiconductor light-emitting device having an n-type contact layer, a light-emitting layer and a p-type contact layer on a substrate, wherein the method comprises, during lowering temperature after completion of growth of the p-type contact layer composed of AlGaN containing a p-type dopant,

immediately after the completion of the growth, starting, at a temperature at which the growth has been completed, supply of a carrier gas composed of an inert gas and reduction of the flow rate of a nitrogen source; and

stopping supply of the nitrogen source at 700 to 950°C in the course of lowering temperature.

16. (new): A production method according to claim 15, wherein the temperature when the growth has been completed is 900°C or higher.

17. (new): A production method according to claim 15, wherein the nitrogen source is ammonia gas.

18. (new): A production method according to claim 15, wherein the carrier gas employed during growth of the semiconductor contains hydrogen gas.

19. (new): A production method according to claim 15, wherein the flow rate of the nitrogen source after the reduction is 0.001 to 10% with respect to the flow rate of the total volume of gas.

20. (new): A Group III nitride semiconductor light-emitting device comprising a substrate; an n-type contact layer, a light-emitting layer, and a p-type contact layer, the layers being provided atop the substrate and being formed of a Group III nitride semiconductor; a negative electrode provided on the n-type contact layer; and a positive electrode provided on the p-type contact layer, wherein the p-type contact layer is composed of a p-type Group III nitride semiconductor according to claim 14.

21. (new): A light-emitting device according to claim 20, wherein the positive electrode is formed of a platinum group metal selected from among Pd, Pt, Rh, Os, Ir, and Ru.

22. (new): A light-emitting device according to claim 20, which is of a flip-chip type.

23. (new): A light-emitting device according to claim 23, which is of a face-up type.